# **Quad 2-Channel Multiplexer** with 3-State Outputs

The MC74VHC257 is an advanced high speed CMOS quad 2-channel multiplexer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

It consists of four 2-input digital multiplexers with common select (S) and enable  $(\overline{OE})$  inputs. When  $(\overline{OE})$  is held High, selection of data is inhibited and all the outputs go Low.

The select decoding determines whether the A or B inputs get routed to the corresponding Y outputs.

The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

- High Speed:  $t_{PD} = 4.1 \text{ ns (Typ)}$  at  $V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 4.0 \mu A$  (Max) at  $T_A = 25$ °C
- High Noise Immunity:  $V_{NIH} = V_{NIL} = 28\% \ V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2.0 V to 5.5 V Operating Range
- Low Noise:  $V_{OLP} = 0.8 \text{ V (Max)}$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: FETs = 100; Equivalent Gates = 25
- These Devices are Pb-Free and are RoHS Compliant

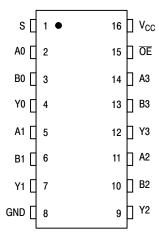


Figure 1. Pin Assignment



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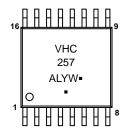
#### MARKING DIAGRAMS











= Assembly Location

L, WL = Wafer Lot

Y, YY = Year

W, WW = Work Week

G or ■ = Pb-Free Package

#### ORDERING INFORMATION

Device	Package	Shipping
MC74VHC257DG	SO-16	48 Units/Rail
MC74VHC257DR2G	SO-16	2500 Units/Reel
MC74VHC257DTG	TSSOP-16	96 Units/Rail
MC74VHC257DTR2G	TSSOP-16	2500 Units/Reel

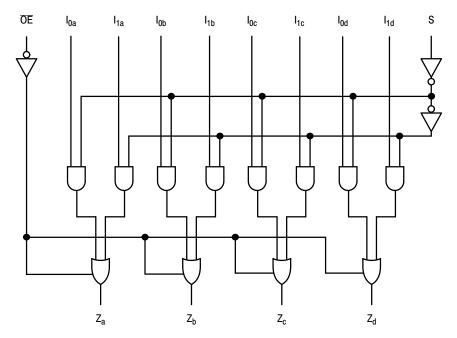


Figure 2. Expanded Logic Diagram

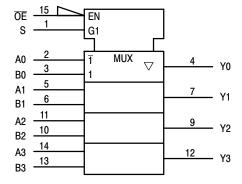


Figure 3. IEC Logic Symbol

# **FUNCTION TABLE**

Inp	Inputs				
ŌĒ	S	Outputs Y0 – Y3			
Н	Х	Z			
L	L	A0-A3			
L	Н	B0-B3			

A0 - A3, B0 - B3 = the levels of the respective Data–Word Inputs.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ . Unused inputs must always be

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

#### **MAXIMUM RATINGS**

Symbol	Pa	rameter	Value	Unit
V <sub>CC</sub>	Positive DC Supply Voltage		-0.5 to +7.0	V
V <sub>IN</sub>	Digital Input Voltage		-0.5 to +7.0	V
V <sub>OUT</sub>	DC Output Voltage	-0.5 to V <sub>CC</sub> +0.5	V	
I <sub>IK</sub>	Input Diode Current	-20	mA	
I <sub>OK</sub>	Output Diode Current	±20	mA	
I <sub>OUT</sub>	DC Output Current, per Pin	± 25	mA	
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins		± 75	mA
$P_{D}$	Power Dissipation in Still Air	SOIC Package TSSOP	200 180	mW
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3)	>2000 >200 >2000	V
I <sub>LATCHUP</sub>	Latchup Performance	Above V <sub>CC</sub> and Below GND at 125°C (Note 4)	±300	mA
$\theta_{JA}$	Thermal Resistance, Junction-to-Ambie	ent SOIC Package TSSOP	143 164	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1 Tested to EIA/JESD22-A114-A
- 2 Tested to EIA/JESD22-A115-A
- 3 Tested to JESD22-C101-A
- 4 Tested to EIA/JESD78

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit	
V <sub>CC</sub>	DC Supply Voltage		2.0	5.5	V
V <sub>IN</sub>	DC Input Voltage		0	5.5	V
V <sub>OUT</sub>	DC Output Voltage		0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature Range, all Package Types		-55	125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise or Fall Time	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0	100 20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

# DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

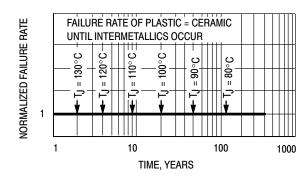


Figure 4. Failure Rate vs. Time Junction Temperature

# **DC CHARACTERISTICS** (Voltages Referenced to GND)

			V <sub>CC</sub>	٦	T <sub>A</sub> = 25°(	C	$T_A \le 85^{\circ}C$		-55°C ≤ T <sub>A</sub> ≤ 125°C		
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High-Level		2.0	1.5			1.5	1.5	1.5		V
	Input Voltage		3.0 to 5.5	V <sub>CCX</sub> 0.7			V <sub>CCX</sub> 0.7	V <sub>CCX</sub> 0.7	V <sub>CCX</sub> 0.7		
$V_{IL}$	Maximum Low-Level		2.0			0.5		0.5		0.5	V
	Input Voltage		3.0 to 5.5			V <sub>CCX</sub> 0.3		V <sub>CCX</sub> 0.3		V <sub>CCX</sub> 0.3	
V <sub>OH</sub>	Maximum High-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50  \mu\text{A}$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		٧
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.8		2.34 3.66		
V <sub>OL</sub>	Maximum Low–Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50  \mu\text{A}$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = 4 \text{ mA}$ $I_{OH} = 8 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I <sub>IN</sub>	Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μΑ
I <sub>OZ</sub>	Maximum 3–State Leakage Current	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$	5.5			±0.25		±2.5		±2.5	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current (per package)	$V_{IN} = V_{CC}$ or GND	5.5			4.0		40.0		40.0	μΑ

# AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ns}$ )

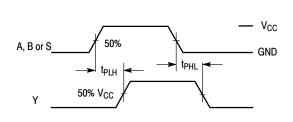
				Т	T <sub>A</sub> = 25°C		<b>T</b> <sub>A</sub> = ≤	85°C	-55°C ≤ T	<sub>A</sub> ≤ 125°C	
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15 pF$ $C_L = 50 pF$		5.8 8.3	9.3 12.8	1.0 1.0	11.0 14.5	1.0 1.0	11.0 14.5	ns
	A or B to Y	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	$C_L = 15 pF$ $C_L = 50 pF$		3.6 5.1	5.9 7.9	1.0 1.0	7.0 9.0	1.0 1.0	7.0 9.0	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15 pF$ $C_L = 50 pF$		7.0 9.5	11.0 14.5	1.0 1.0	13.0 16.5	1.0 1.0	13.0 16.5	ns
	S to Y	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	$C_L = 15 pF$ $C_L = 50 pF$		4.0 5.5	6.8 8.8	1.0 1.0	8.0 10.0	1.0 1.0	8.0 10.0	
t <sub>PZL</sub> , t <sub>PZH</sub>	Maximum Output Enable Time	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_L = 1 \text{ k}\Omega$	$C_L = 15 pF$ $C_L = 50 pF$		6.7 9.2	10.5 14.0	1.0 1.0	12.5 16.0	1.0 1.0	12.5 16.0	ns
	ŌE to Y	$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $R_L = 1 \text{ k}\Omega$			3.6 5.1	6.8 8.8	1.0 1.0	8.0 10.0	1.0 1.0	8.0 10.0	
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Maximum Output Disable Time	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_L = 1 \text{ k}\Omega$	C <sub>L</sub> = 50 pF		12.0	15.0	1.0	16.0	1.0	17.5	ns
	ŌE to Y	$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $R_L = 1 \text{ k}\Omega$	C <sub>L</sub> = 50 pF		5.7	13.0	1.0	14.0	1.0	15.0	
C <sub>IN</sub>	Maximum Input Capacitance				4	10		10		10	pF

		Typical @ 25°C, V <sub>CC</sub> = 5.0V	
$C_PD$	Power Dissipation Capacitance (Note 5)	20	pF

<sup>5.</sup> C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>. C<sub>PD</sub> is used to determine the no–load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

# **NOISE CHARACTERISTICS** (Input $t_f = t_f = 3.0 \text{ ns}, C_L = 50 \text{ pF}, V_{CC} = 5.0 \text{ V})$

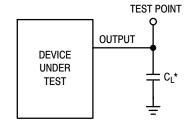
		T <sub>A</sub> = 25°C		
Symbol	Characteristic	Тур	Max	Unit
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.3	0.8	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	- 0.3	- 0.8	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		3.5	V
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		1.5	V



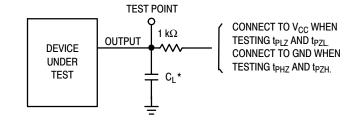
 $\nu_{\text{CC}}$ ΟE 50% GND ← t<sub>PZL</sub>  $t_{PLZ}-$ HIGH **IMPEDANCE** 50% V<sub>CC</sub>  $V_{OL} + 0.3V$ t<sub>PHZ</sub>→  $t_{PZH}$ V<sub>OH</sub> - 0.3V 50% V<sub>CC</sub> HIGH **IMPEDANCE** 

Figure 5. Switching Waveform

Figure 6. Switching Waveform



\*Includes all probe and jig capacitance



\*Includes all probe and jig capacitance

Figure 7. Test Circuit

Figure 8. Test Circuit

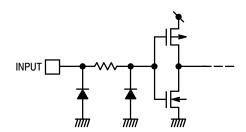
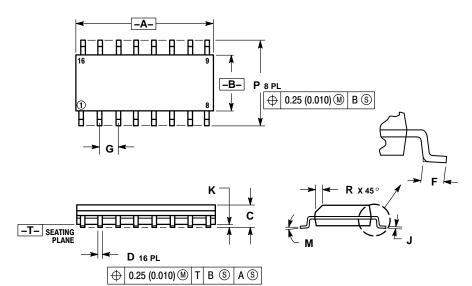


Figure 9. Input Equivalent Circuit

# **PACKAGE DIMENSIONS**

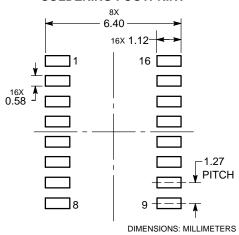
SOIC-16 CASE 751B-05 ISSUE K



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
  4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
  5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION AND SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

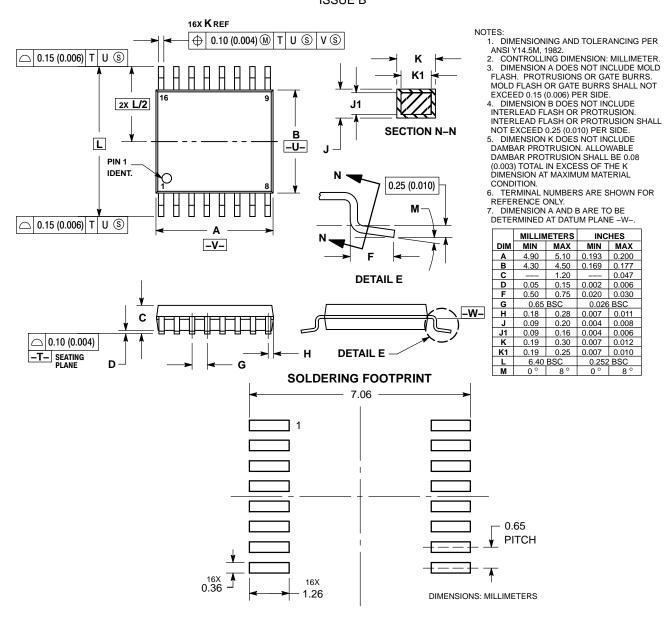
	MILLIN	IETERS	INC	HES		
DIM	MIN	MAX	MIN	MAX		
Α	9.80	10.00	0.386	0.393		
В	3.80	4.00	0.150	0.157		
С	1.35	1.75	0.054	0.068		
D	0.35 0.49		0.014	0.019		
F	0.40	1.25	0.016	0.049		
G	1.27	BSC	0.050	BSC		
J	0.19	0.25	0.008	0.009		
K	0.10 0.25		0.004	0.009		
M	0°	7°	0°	7°		
Р	5.80	6.20	0.229	0.244		
R	0.25	0.50	0.010	0.019		

# **SOLDERING FOOTPRINT**



#### PACKAGE DIMENSIONS

### TSSOP-16 CASE 948F ISSUE B



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